L Number	Hits	Search Text	DB	Time stamp
1	94	(438/963).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 15:00
8	5	((438/963).CCLS.) and 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 15:01
9	13	@ad<=19990219 and (438/759).ccls. and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 15:04
-	12	(("6207583") or ("6303513") or ("5669979") or ("5814156") or ("4548688")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:31
-	10	((("6207583") or ("6303513") or ("5669979") or ("5814156") or ("4548688")).PN.) and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 09:08
-	100827	'photoresist' or 'photoreactive' near 'flourine containing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 09:14
-	82441	('photoresist' or 'photoreactive' near 'flourine containing') and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 09:17
-	7631	(('photoresist' or 'photoreactive' near 'flourine containing') and @ad<=19990219) and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:25
-	149	(('photoresist' or 'photoreactive' near 'flourine containing') and @ad<=19990219) and 'ammonia' and 'plasma ashing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:24
-	283	'cleaning process' and @ad<=19990219 and 'fluorine containing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:31
-	67	('cleaning process' and @ad<=19990219 and 'fluorine containing') and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:20
-	234187	(("438") or ("257")).CLAS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:01
-	2	(((438/$) or (257/$)).CCLS.) and 'volatilize residue'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:23
-	33	(((438/$) or (257/$)).CCLS.) and 'dry cleaning' and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:30

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–	1130	(((438/$) or (257/$)).CCLS.) and 'ammonia' and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:34
–	10	((((438/$) or (257/$)).CCLS.) and 'ammonia' and 'ultraviolet') and 'volatilize'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:34
–	30	((('cleaning process' and @ad<=19990219 and 'fluorine containing') and 'ultraviolet') and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:51
–	51	(((438/$) or (257/$)).CCLS.) and 'residue removal' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:02
–	876	(((438/$) or (257/$)).CCLS.) and 'ammonia' and 'ultraviolet' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:04
–	7	((((438/$) or (257/$)).CCLS.) and 'ammonia' and 'ultraviolet' and @ad<=19990219) and 'dry cleaning'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:24
–	280	(134/1.1).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:09
–	3680	(134/1-4).ccls. and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:44
–	6	((134/1-4).ccls. and @ad<=19990219) and 'ultraviolet' and 'ammonia gas'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:07
–	11	((134/1-4).ccls. and @ad<=19990219) and 'fluorine residue'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:06
–	161	(438/715).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:43
–	3	((438/715).ccls.) and @ad<19990219 and 'volatilize'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:12
–	7	(("5129958") or ("5935340") or ("5207836")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:16
–	714	'fluorine' with 'photoresist'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:19

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		514	('fluorine' with 'photoresist') and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:18
-		0	'photoresist containing fluorine' and @ad<=1999019	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:19
-		188	'ashing photoresist' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:04
-		65	('ashing photoresist' and @ad<=19990219) and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:52
-		0	(('ashing photoresist' and @ad<=19990219) and 'ultraviolet') and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:53
-		0	(('ashing photoresist' and @ad<=19990219) and 'ultraviolet') and 'NH3'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:53
-		0	'cleaning photoresist' with 'flourine containing' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:25
-		0	removal adj 'flourine containing residue' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:17
-		0	removal adj 'flourine containing' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:18
-		71	'removal' and 'flourine containing' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:18
-		0	('cleaning process' and @ad<=19990219 and 'fluorine containing') and 'ultraviolet' near 'simultaneous'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:21
-		8	@ad<=19990219 and 'fluorine containing residue'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:21
-		529	'organic photoresist' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:50
-		47	('organic photoresist' and @ad<=19990219) and 'ultraviolet' and 'simultaneous' and 'gas'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:54

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-	512982	cleaning or removal same 'organic photoresist' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:42
-	28	cleaning same 'organic photoresist' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:54
-	11	'organic photoresist' with 'fluorine' and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:38
-	1483	(cleaning or removal same 'organic photoresist' and @ad<=19990219) and 'ultraviolet' and 'simultaneous'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:41
-	437	((cleaning or removal same 'organic photoresist' and @ad<=19990219) and 'ultraviolet' and 'simultaneous') and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:48
-	2	("6272768").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:15
-	0	removal same 'polymer residue' same 'fluorine' and @ad<=19990219 and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:54
-	0	'polymer residue' same 'fluorine' and @ad<=19990219 and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:54
-	10	'polymer residue' and 'fluorine' and @ad<=19990219 and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:55
-	162	'fluorine containing polymer' and @ad<=19990219 and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:24
-	1	'cleaning' with 'fluorine containing polymer' and @ad<=19990219 and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:25
-	2	("6272768").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:42
-	1	"4643774".PN.	USPAT	2002/11/12 11:45
-	1	"4714086".PN.	USPAT	2002/11/12 11:45
-	1	"4735000".PN.	USPAT	2002/11/12 11:45
-	1	"4736760".PN.	USPAT	2002/11/12 11:46
-	1	"4984597".PN.	USPAT	2002/11/12 11:46
-	1	"5217559".PN.	USPAT	2002/11/12 11:46

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	1	"5232511".PN.	USPAT	2002/11/12 11:47
–	124	@ad<=19990219 and 'ultraviolet' same 'simultaneous' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:50
–	1	@ad<=19990219 and 'substrate cleaning' and 'ultraviolet' same 'simultaneous' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:53
–	4	@ad<=19990219 and 'semiconductor substrate' and 'ultraviolet' same 'simultaneous' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:07
–	5	@ad<=19990219 and 'semiconductor substrate' same 'cleaning' and 'ultraviolet' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:12
–	8	@ad<=19990219 and 'substrate cleaning' and 'ultraviolet' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:02
–	184	(438/715).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:44
–	184	(438/715).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:44
–	3732	(134/1-4).ccls. and @ad<=19990219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:51
–	774	((438/691) or (438/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:10
–	184	(438/715).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:47
–	1216	((438/693) or (438/974) or (204/510)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:49
–	94	((134/1-4).ccls. and @ad<=19990219) and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:51
–	18	(((438/691) or (438/906)).CCLS.) and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:52
–	3	((438/715).CCLS.) and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:52

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-	17	(((438/693) or (438/974) or (204/510)).CCLS.) and 'ultraviolet' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:11
-	10	(("6207583") or ("6303513") or ("5669979") or ("5814156") or ("4548688")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:32
-	460	'cleaning' same 'photoresist' and @ad<=19990219 and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:43
-	8	@ad<=19990219 and 'cleaning' same 'photoresist' same 'gas' same 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:49
-	80	@ad<=19990219 and 'removal' same 'photoresist' same 'gas' same 'water'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 11:57
-	64	@ad<=19990219 and 'removal' same 'organic' same 'gas' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:56
-	29	@ad<=19990219 and 'removal' same 'organic' same 'gas' same 'water' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:57
-	23	@ad<=19990219 and 'removal' same 'photoresist' same 'gas' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:57
-	2	@ad<=19990219 and 'removal' same 'resist' same 'gas' same 'water' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 10:58
-	468	@ad<=19990219 and 'clean' and 'photoresist' and 'ammonia' and 'water' and 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 11:50
-	2	@ad<=19990219 and 'removal' same 'photoresist' same 'ammonia' same 'water' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:55
-	2	@ad<=19990219 and 'clean' same 'photoresist' same 'gas' same 'water' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 11:54
-	1	@ad<=19990219 and 'removal' same 'photoresist' same 'gas' same 'water' same 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 11:54
-	19	@ad<=19990219 and 'removal' same 'photoresist' same 'gas' same 'water' and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:05

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—		17	@ad<=19990219 and 'removal' same 'photoresist' same 'hydrogen' same 'water' and 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:49
—		387	(134/1.1).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:10
—		1790	(134/1).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:13
—		282	(134/1.2).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:13
—		626	(134/1.3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:14
—		892	((438/691) or (438/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:01
—		1304	(((438/693) or (438/974) or (204/510)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:18
—		18	@ad<=19990219 and 'photoresist' same 'hydrogen' same 'water' same 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:52
—		2	@ad<=19990219 and 'removal' same 'photoresist' same 'ammonia' same 'water' same 'Ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:56
—		39	@ad<=19990219 and 'removal' same 'photoresist' same 'ultraviolet' same 'plasma'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:57
—		12	@ad<=19990219 and 'removal' same 'photoresist' same 'ultraviolet' same 'plasma' and 'hydrogen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 12:57
—		11	@ad<=19990219 and 'removal' same 'photoresist' same 'ultraviolet' same 'plasma' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:05
—		31	@ad<=19990219 and 'removal' same 'photoresist' same 'UV' same 'plasma' and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:10
—		2	@ad<=19990219 and 'removal' same 'photoresist' same 'UV' same 'plasma' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:11

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–		13	@ad<=19990219 and 'removal' same 'photoresist' same 'UV' same 'plasma' same 'hydrogen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:14
–		1	@ad<=19990219 and 'removal' same 'photoresist' same 'UV' same 'plasma' same 'sulfur dioxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:37
–		2	("4778536").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:28
–		0	@ad<=19990219 and 'cleaning' same 'photoresist' same 'UV' same 'sulfur dioxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:37
–		20	@ad<=19990219 and 'cleaning' same 'photoresist' same 'UV' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:50
–		1	@ad<=19990219 and 'cleaning' same 'photoresist' same 'UV' with 'hydrogen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:38
–		2	("4548688").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 08:50
–		963	((438/691) or (438/906)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 14:50
–		47	'ashing photoresist' and @ad<=19990219 and 'residue' and 'UV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:04
–		47	'ashing photoresist' and @ad<=19990219 and 'residue' and 'UV' and 'gas'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:10
–		1	'ashing' same 'photoresist' same 'plasma' and @ad<=19990219 and 'remove' same 'residue' same 'Ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:11
–		0	'ashing' same 'photoresist' same 'plasma' and @ad<=19990219 and 'clean' same 'residue' same 'Ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:11
–		47	@ad<=19990219 and 'clean' same 'residue' same 'ultraviolet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:15
–		25	@ad<=19990219 and 'remove' same 'residue' same 'ultraviolet' same 'gas'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:13

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		2	@ad<=19990219 and 'photoresist' and 'remove' same 'residue' same 'ultraviolet' same 'gas'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:57
–		8	@ad<=19990219 and 'photoresist' same 'residue' same 'ultraviolet' same 'hydrogen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:50
–		11	@ad<=19990219 and 'removal' same 'residue' same 'ultraviolet' same 'hydrogen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:50
–		2	@ad<=19990219 and 'remove' same 'residue' same 'ultraviolet' same 'sulfur dioxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:51
–		7	@ad<=19990219 and 'removal' same 'residue' same 'ultraviolet' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 15:01
–		11	@ad<=19990219 and 'removal' same 'residue' same 'ultraviolet' same 'hydrogen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:53
–		3	@ad<=19990219 and 'photoresist' and 'residue' same 'ultraviolet' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 13:59
–		19	@ad<=19990219 and 'photoresist' and 'remove' same 'residue' and 'ultraviolet' same 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 14:00
–		162	(438/759).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 14:59

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